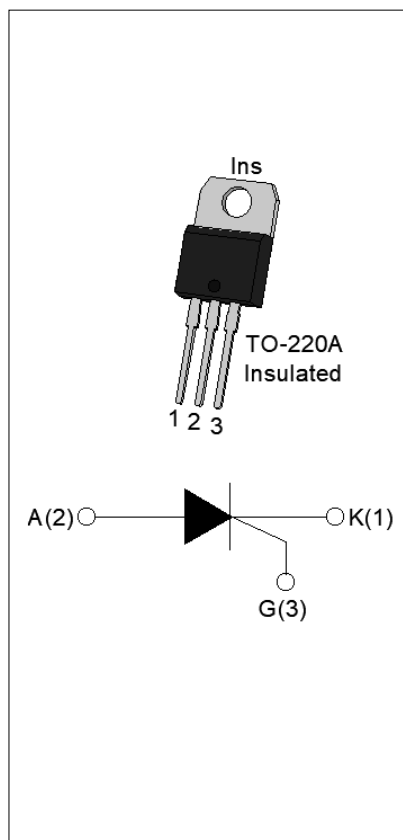




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151A-800R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT151A-800R provides a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906).
Package TO-220A is RoHS compliant.



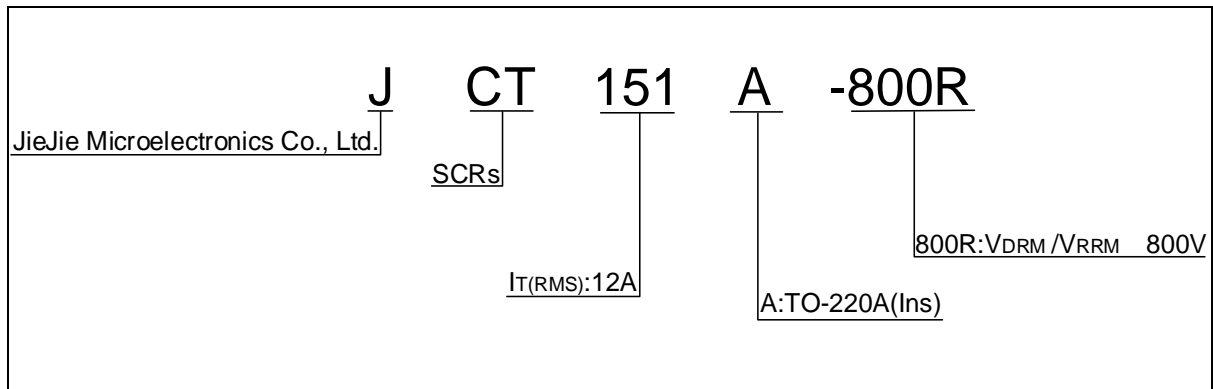
MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	"15	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
Average on-state current ($T_c = 95^\circ C$)	$I_{T(AV)}$	7.5	A
RMS on-state current ($T_c = 95^\circ C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	120	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		132	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	100	A/s

ORDERING INFORMATION



MARKING

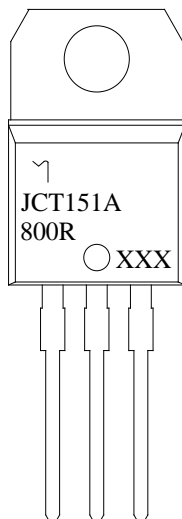
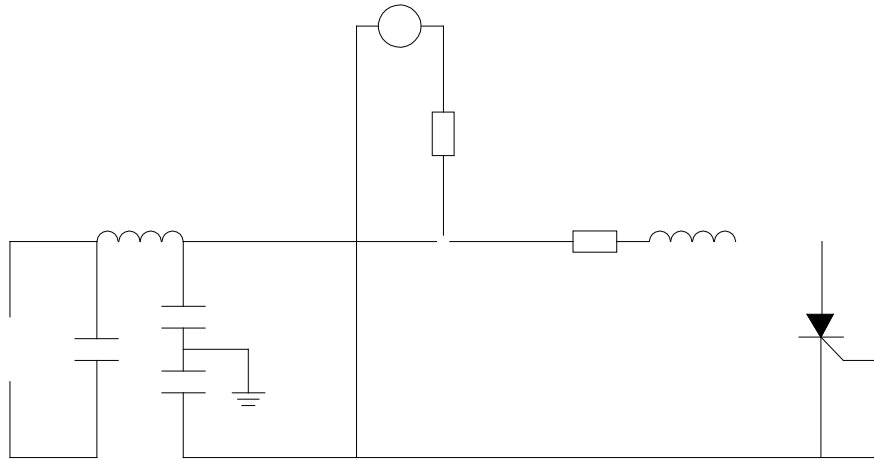


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)		Package	
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Information furnished in this document is believed to be accurate and reliable.
However, Jiangsu JieJie Microelectronics Co., Ltd.